Ordering number: EN3280



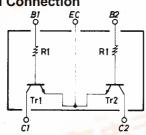
FC126

NPN Epitaxial Planar Silicon Composite Transistor
Switching Applications
(with Bias Resistance)

Features

- · On-chip bias resistance (R1=47k Ω).
- · Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC126 is formed with two chips, being equivalent to the 2SC3898, placed in one package.
- · Excellent in thermal equilibrium and pair capability.

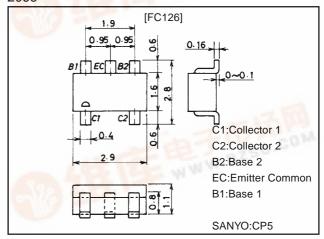
Electrical Connection



Package Dimensions

unit:mm

2066



Specifications

Absolute Maximum Ratings at Ta = 25°C

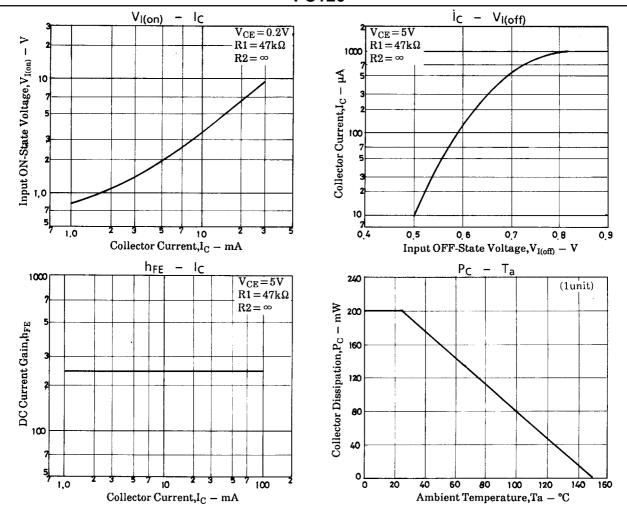
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		50	V
Collector-to-Emitter Voltage	VCEO	and the Colombian Late	50	V
Emitter-to-Base Voltage	V _{EBO}	ATT THE W	5	V
Collector Current	IC	130 / 4 - 4 - 4	100	mA
Peak Collector Current	ICP	LRO MANUEL MANUE	200	mA
Collector Dissipation	PC	1 unit	200	mW
Total Power Dissipation	PT	Care	300	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditons	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =40V, I _E =0		- 0.7	0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0	and Mil	41.0	0.1	μΑ
DC Current Gain	hFE	V _{CE} =5V, I _C =10mA	100			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =5mA		250		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		3.3		pF
C-E Saturation Voltage	VCE(sat)	I _C =5mA, I _B =0.25mA		0.1	0.3	V
C-B Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0	50			V
C-E Breakdown Voltage	V(BR)CEO	I _C =100μA, R _{BE} =∞	50			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} =5V, I _C =100μA	0.4	0.55	0.8	V
Input ON-State Voltage	V _{I(on)}	V _{CE} =0.2V, I _C =5mA	0.8	2.0	4.0	V
Input Resistance	R1		33	47	61	kΩ

Note: The specifications shown above are for each individual transistor.

Marking:126



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